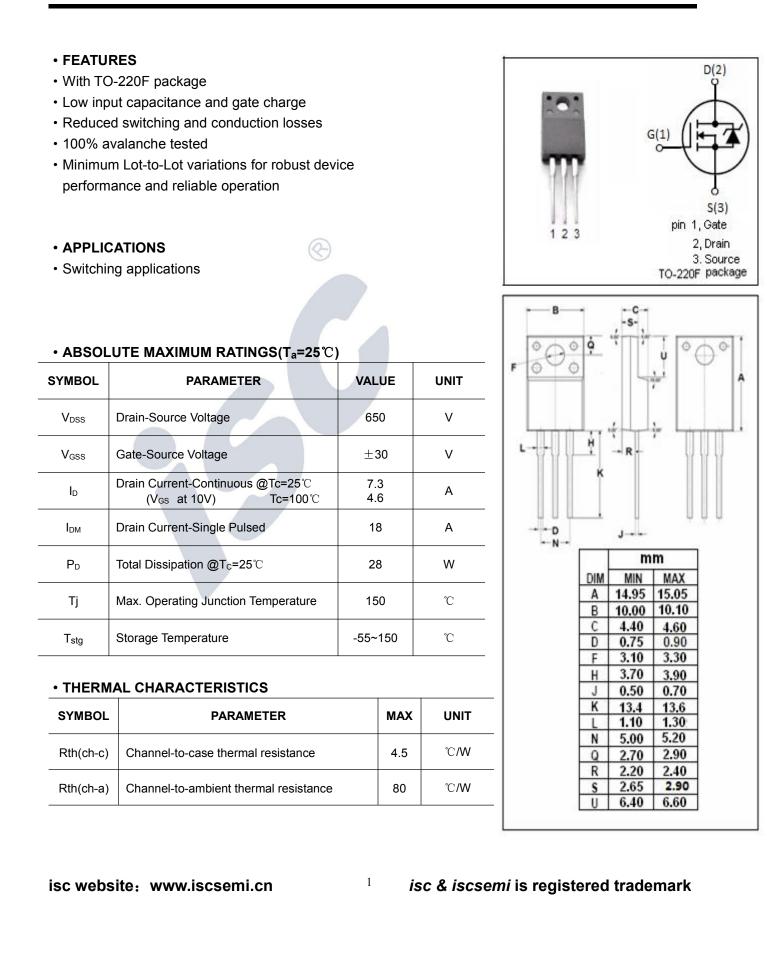


INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

IPA65R600C6





Isc N-Channel MOSFET Transistor

IPA65R600C6

ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	650			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =0.21mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =2.1A		540	600	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V;V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 650V; V _{GS} = 0V;Tj=25℃ V _{DS} = 650V; V _{GS} = 0V; Tj=150℃			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =3.2A, V _{GS} = 0V		0.9		V

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